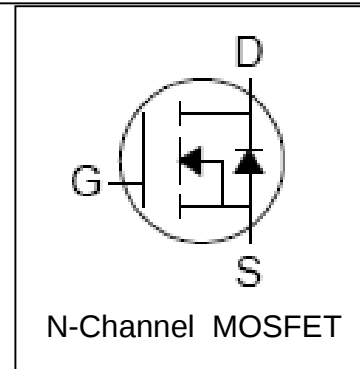
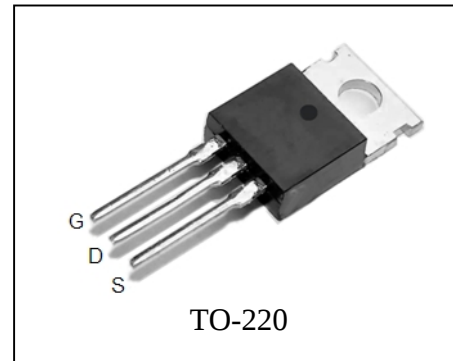


## Features

- 75V/148A,  
 $R_{DS(ON)} = 5.5m\Omega(Typ.) @ V_{GS}=10V$
- Super High Dense Cell Design
- Ultra Low On-Resistance
- 100% avalanche tested
- Lead Free and Green Devices Available  
(RoHS Compliant)

## Pin Description



## Applications

- Switching Application Systems
- UPS

## Absolute Maximum Ratings

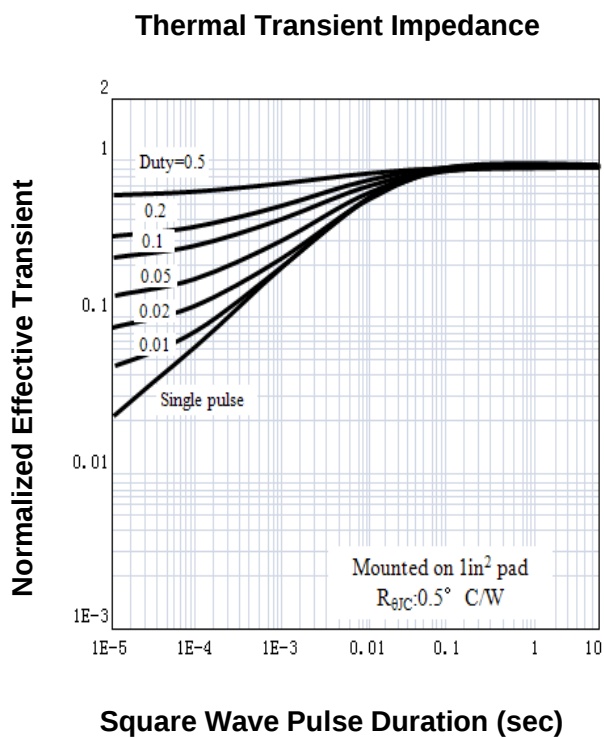
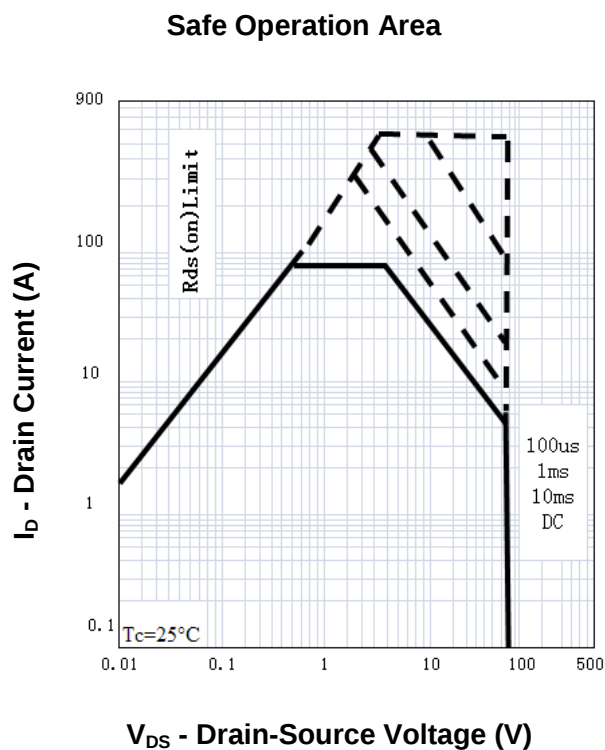
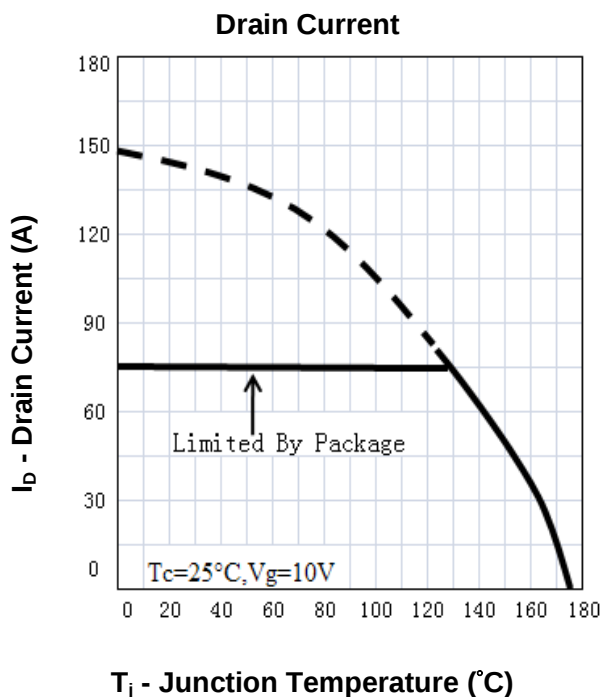
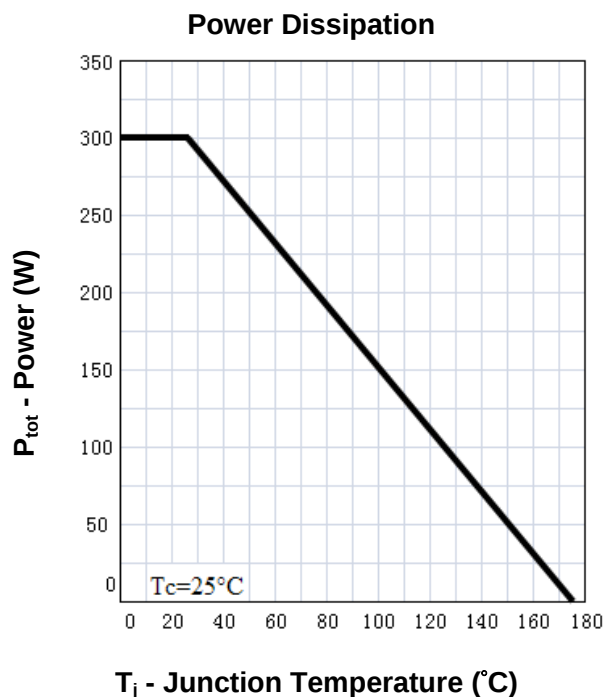
| Symbol                                                       | Parameter                                      |                       | Rating           | Unit |
|--------------------------------------------------------------|------------------------------------------------|-----------------------|------------------|------|
| Common Ratings (T <sub>C</sub> =25°C Unless Otherwise Noted) |                                                |                       |                  |      |
| V <sub>DSS</sub>                                             | Drain-Source Voltage                           |                       | 75               | V    |
| V <sub>GSS</sub>                                             | Gate-Source Voltage                            |                       | ±25              |      |
| T <sub>J</sub>                                               | Maximum Junction Temperature                   |                       | 175              | °C   |
| T <sub>STG</sub>                                             | Storage Temperature Range                      |                       | -55 to 175       | °C   |
| I <sub>S</sub>                                               | Diode Continuous Forward Current               | T <sub>C</sub> =25°C  | 148 <sup>①</sup> | A    |
| Mounted on Large Heat Sink                                   |                                                |                       |                  |      |
| I <sub>DP</sub>                                              | 300μs Pulse Drain Current Tested               | T <sub>C</sub> =25°C  | 592 <sup>②</sup> | A    |
| I <sub>D</sub>                                               | Continuous Drain Current(V <sub>GS</sub> =10V) | T <sub>C</sub> =25°C  | 148 <sup>①</sup> | A    |
|                                                              |                                                | T <sub>C</sub> =100°C | 110 <sup>①</sup> |      |
| P <sub>D</sub>                                               | Maximum Power Dissipation                      | T <sub>C</sub> =25°C  | 300              | W    |
|                                                              |                                                | T <sub>C</sub> =100°C | 150              | W    |
| R <sub>θJC</sub>                                             | Thermal Resistance-Junction to Case            |                       | 0.5              | °C/W |
| Drain-Source Avalanche Ratings                               |                                                |                       |                  |      |
| E <sub>AS</sub> <sup>③</sup>                                 | Avalanche Energy, Single Pulsed                |                       | 784              | mJ   |

**Electrical Characteristics** (T<sub>C</sub>=25°C Unless Otherwise Noted)

| Symbol                       | Parameter                        | Test Condition                                                                                                         | RU75150R |      |      | Unit |
|------------------------------|----------------------------------|------------------------------------------------------------------------------------------------------------------------|----------|------|------|------|
|                              |                                  |                                                                                                                        | Min.     | Typ. | Max. |      |
| Static Characteristics       |                                  |                                                                                                                        |          |      |      |      |
| BV <sub>DSS</sub>            | Drain-Source Breakdown Voltage   | V <sub>GS</sub> =0V, I <sub>DS</sub> =250μA                                                                            | 75       |      |      | V    |
| I <sub>DSS</sub>             | Zero Gate Voltage Drain Current  | V <sub>DS</sub> = 75V, V <sub>GS</sub> =0V                                                                             |          |      | 1    | μA   |
|                              |                                  | T <sub>J</sub> =85°C                                                                                                   |          |      | 30   |      |
| V <sub>GS(th)</sub>          | Gate Threshold Voltage           | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =250μA                                                              | 2        | 3    | 4    | V    |
| I <sub>GSS</sub>             | Gate Leakage Current             | V <sub>GS</sub> =±25V, V <sub>DS</sub> =0V                                                                             |          |      | ±100 | nA   |
| R <sub>DS(ON)</sub> ④        | Drain-Source On-state Resistance | V <sub>GS</sub> = 10V, I <sub>DS</sub> =75A                                                                            |          | 5.5  | 6.5  | mΩ   |
| Diode Characteristics        |                                  |                                                                                                                        |          |      |      |      |
| V <sub>SD</sub> ④            | Diode Forward Voltage            | I <sub>SD</sub> =75A, V <sub>GS</sub> =0V                                                                              |          |      | 1.2  | V    |
| t <sub>rr</sub>              | Reverse Recovery Time            | I <sub>SD</sub> =75A, dI <sub>SD</sub> /dt=100A/μs                                                                     |          | 43   |      | ns   |
| Q <sub>rr</sub>              | Reverse Recovery Charge          |                                                                                                                        |          | 65   |      | nC   |
| Dynamic Characteristics⑤     |                                  |                                                                                                                        |          |      |      |      |
| R <sub>G</sub>               | Gate Resistance                  | V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, F=1MHz                                                                       |          | 1.2  |      | Ω    |
| C <sub>iss</sub>             | Input Capacitance                | V <sub>GS</sub> =0V,<br>V <sub>DS</sub> = 37.5V,<br>Frequency=1.0MHz                                                   |          | 6800 |      | pF   |
| C <sub>oss</sub>             | Output Capacitance               |                                                                                                                        |          | 780  |      |      |
| C <sub>rss</sub>             | Reverse Transfer Capacitance     |                                                                                                                        |          | 210  |      |      |
| t <sub>d(ON)</sub>           | Turn-on Delay Time               | V <sub>DD</sub> =37.5V, R <sub>L</sub> =0.5Ω,<br>I <sub>DS</sub> =75A, V <sub>GEN</sub> = 10V,<br>R <sub>G</sub> =4.7Ω |          | 21   |      | ns   |
| t <sub>r</sub>               | Turn-on Rise Time                |                                                                                                                        |          | 78   |      |      |
| t <sub>d(OFF)</sub>          | Turn-off Delay Time              |                                                                                                                        |          | 68   |      |      |
| t <sub>f</sub>               | Turn-off Fall Time               |                                                                                                                        |          | 42   |      |      |
| Gate Charge Characteristics⑤ |                                  |                                                                                                                        |          |      |      |      |
| Q <sub>g</sub>               | Total Gate Charge                | V <sub>DS</sub> =60V, V <sub>GS</sub> = 10V,<br>I <sub>DS</sub> =75A                                                   |          | 138  |      | nC   |
| Q <sub>gs</sub>              | Gate-Source Charge               |                                                                                                                        |          | 42   |      |      |
| Q <sub>gd</sub>              | Gate-Drain Charge                |                                                                                                                        |          | 56   |      |      |

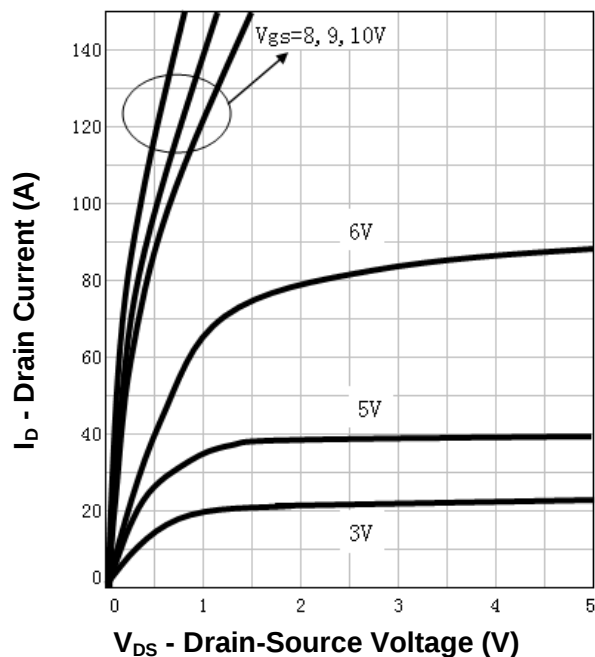
- Notes:
- ① Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 75A.
  - ② Pulse width limited by safe operating area.
  - ③ Limited by T<sub>Jmax</sub>, I<sub>AS</sub> =56A, V<sub>DD</sub> = 48V, R<sub>G</sub> = 50Ω, Starting T<sub>J</sub> = 25°C.
  - ④ Pulse test ; Pulse width≤300μs, duty cycle≤2%.
  - ⑤ Guaranteed by design, not subject to production testing.

## Typical Characteristics

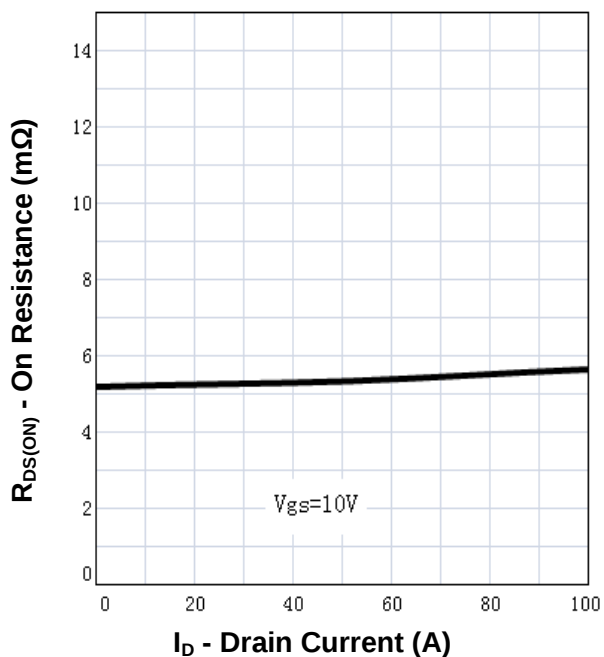


## Typical Characteristics

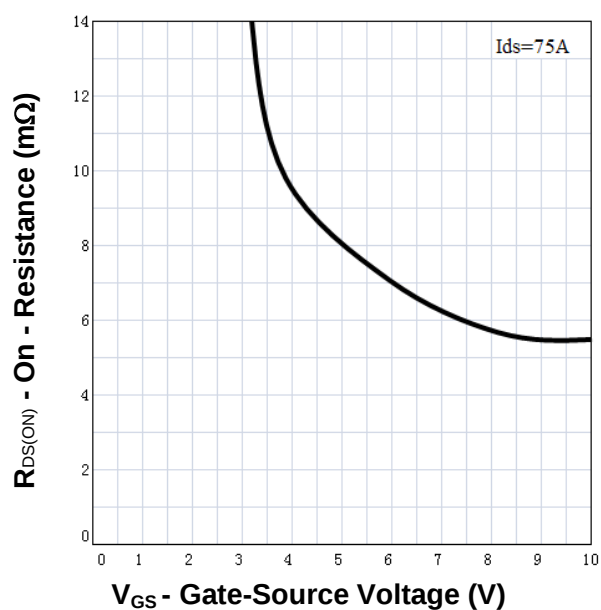
Output Characteristics



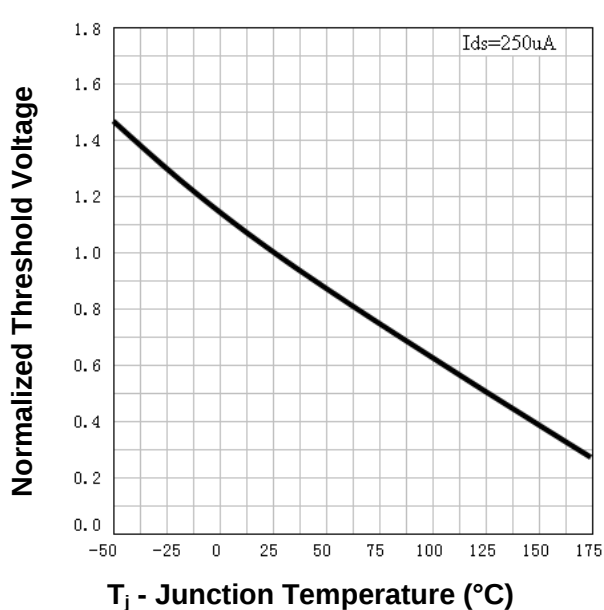
Drain-Source On Resistance



Drain-Source On Resistance

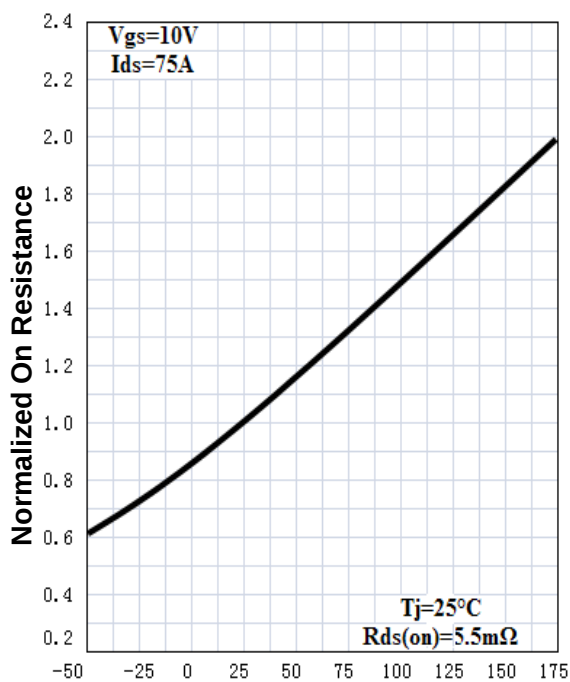


Gate Threshold Voltage



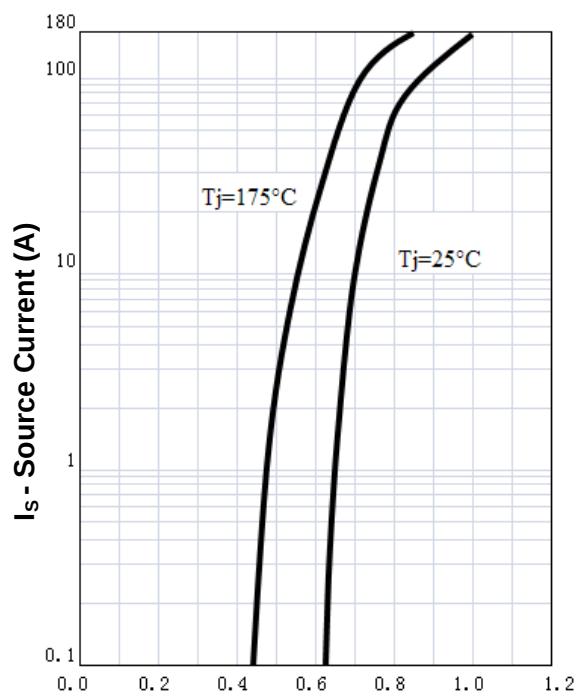
## Typical Characteristics

**Drain-Source On Resistance**



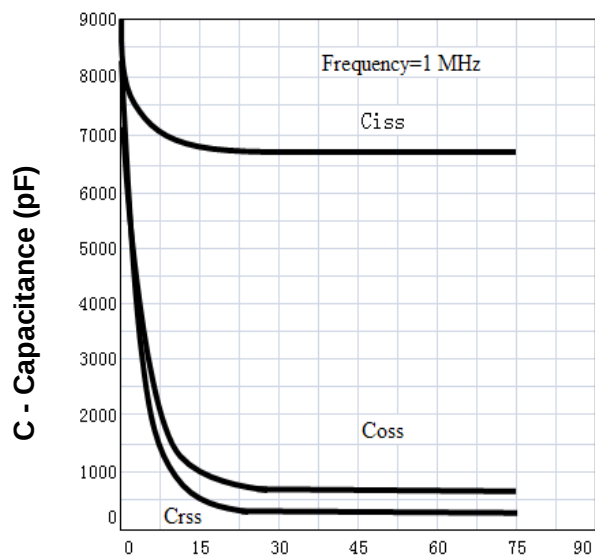
$T_j$  - Junction Temperature ( $^{\circ}\text{C}$ )

**Source-Drain Diode Forward**



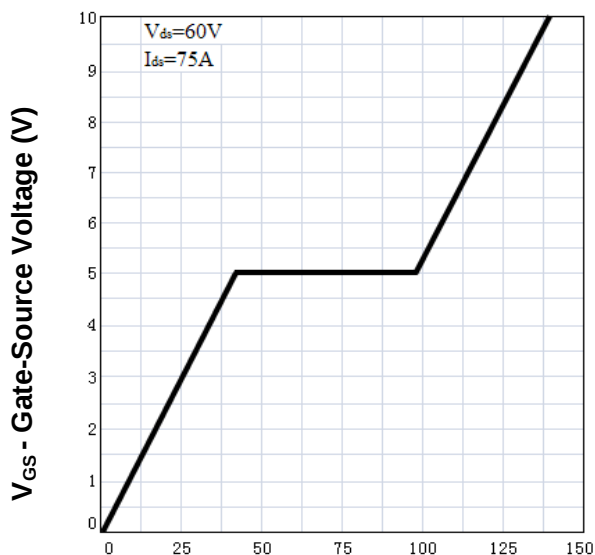
$V_{SD}$  - Source-Drain Voltage (V)

**Capacitance**



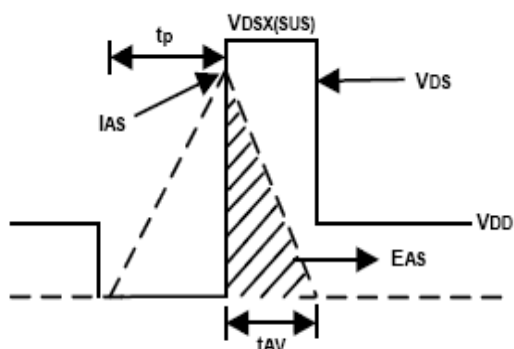
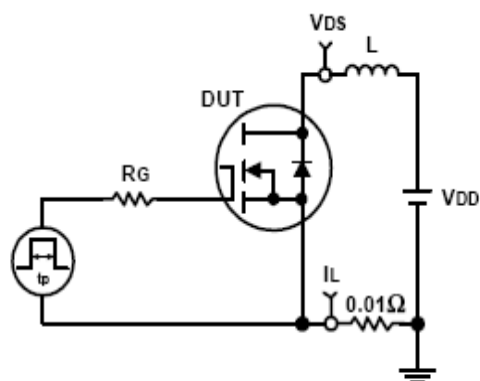
$V_{DS}$  - Drain-Source Voltage (V)

**Gate Charge**

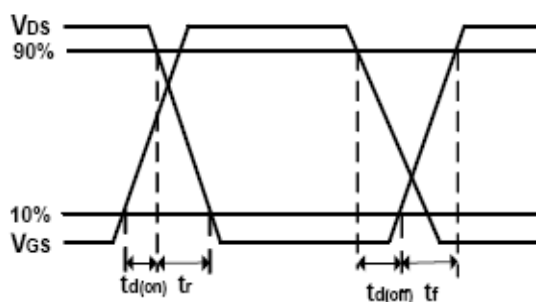
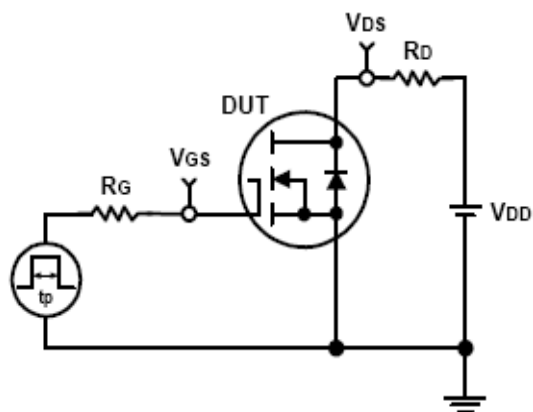


$Q_G$  - Gate Charge (nC)

## Avalanche Test Circuit and Waveforms



## Switching Time Test Circuit and Waveforms

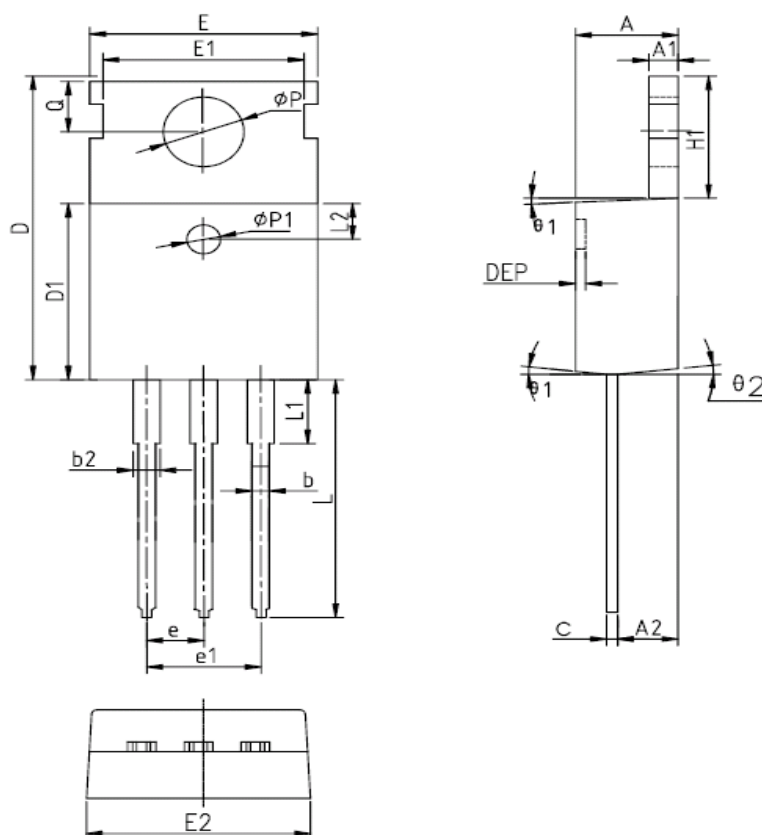


**Ordering and Marking Information**

| Device   | Marking  | Package | Packaging | Quantity | Reel Size | Tape width |
|----------|----------|---------|-----------|----------|-----------|------------|
| RU75150R | RU75150R | TO-220  | Tube      | 50       | -         | -          |

# Package Information

## TO-220FB-3L



| SYMBOL | MM    |       |       | INCH  |       |       | SYMBOL     | MM       |      |       | INCH      |       |       |
|--------|-------|-------|-------|-------|-------|-------|------------|----------|------|-------|-----------|-------|-------|
|        | MIN   | NOM   | MAX   | MIN   | NOM   | MAX   |            | MIN      | NOM  | MAX   | MIN       | NOM   | MAX   |
| A      | 4.40  | 4.57  | 4.70  | 0.173 | 0.180 | 0.185 | $\phi p1$  | 1.40     | 1.50 | 1.60  | 0.055     | 0.059 | 0.063 |
| A1     | 1.27  | 1.30  | 1.33  | 0.050 | 0.051 | 0.052 | e          | 2.54BSC  |      |       | 0.1BSC    |       |       |
| A2     | 2.35  | 2.40  | 2.50  | 0.093 | 0.094 | 0.098 | e1         | 5.08BSC  |      |       | 0.2BSC    |       |       |
| b      | 0.77  | -     | 0.90  | 0.030 | -     | 0.035 | H1         | 6.40     | 6.50 | 6.60  | 0.252     | 0.256 | 0.260 |
| b2     | 1.23  | -     | 1.36  | 0.048 | -     | 0.054 | L          | 12.75    | -    | 13.17 | 0.502     | -     | 0.519 |
| C      | 0.48  | 0.50  | 0.52  | 0.019 | 0.020 | 0.021 | L1         | -        | -    | 3.95  | -         | -     | 0.156 |
| D      | 15.40 | 15.60 | 15.80 | 0.606 | 0.614 | 0.622 | L2         | 2.50REF. |      |       | 0.098REF. |       |       |
| D1     | 9.00  | 9.10  | 9.20  | 0.354 | 0.358 | 0.362 | $\phi p$   | 3.57     | 3.60 | 3.63  | 0.141     | 0.142 | 0.143 |
| DEP    | 0.05  | 0.10  | 0.20  | 0.002 | 0.004 | 0.008 | Q          | 2.73     | 2.80 | 2.87  | 0.107     | 0.110 | 0.113 |
| E      | 9.70  | 9.90  | 10.10 | 0.382 | 0.389 | 0.398 | $\theta_1$ | 5°       | 7°   | 9°    | 5°        | 7°    | 9°    |
| E1     | -     | 8.70  | -     | -     | 0.343 | -     | $\theta_2$ | 1°       | 3°   | 5°    | 1°        | 3°    | 5°    |
| E2     | 9.80  | 10.00 | 10.20 | 0.386 | 0.394 | 0.401 |            |          |      |       |           |       |       |

ALL DIMENSIONS REFER TO JEDEC STANDARD  
DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS

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